

IN THE CLAIMS:

1. (Currently Amended) A semiconductor component, comprising a semiconductor element encased by a cover element having an integrated electroconductive metal element comprising at least one outlet, wherein the at least one outlet is configured to constantly connect the electroconductive metal element to ground in order to shield the semiconductor element against electrostatic pulses.
2. (Previously Presented) A semiconductor component according to claim 1, wherein in structure, the electroconductive metal element is a planar sheet.
3. (Previously Presented) A semiconductor component according to claim 1, wherein the electroconductive metal element is a thin loop structure.
4. (Previously Presented) A semiconductor component according to claim 1, wherein the electroconductive metal element forms a permanent, integrated part of the semiconductor component.
5. (Previously Presented) A semiconductor component according to claim 1, wherein the electroconductive metal element is placed underneath the cover element of the semiconductor component, inside said cover element.
6. (Previously Presented) A semiconductor component according to claim 1, wherein the electroconductive metal element is attached to the cover element of the semiconductor component, outside said cover element.
7. (Previously Presented) A semiconductor component according to claim 1, wherein the electroconductive metal element is induced in the cover element of the semiconductor component either chemically or electrochemically.
8. (Currently Amended) A method for shielding a semiconductor element against electrostatic pulses, comprising: integrating the semiconductor element in a semiconductor component, covering the semiconductor element with a cover element, integrating an electroconductive metal element within the cover element of the semiconductor component and providing at least one outlet for the integrated

electroconductive metal element, so that the at least one outlet is configured to constantly connect the electroconductive metal element to ground.

9. (Previously Presented) A method according to claim 8, wherein in the semiconductor component, there is integrated an electroconductive, planar metal element.

10. (Previously Presented) A method according to claim 8, wherein in the semiconductor component, there is integrated an electroconductive, loop-shaped metal element.

11. (Previously Presented) A method according to claim 8, wherein the electroconductive metal element is integrated as a permanent part of the semiconductor component.

12. (Previously Presented) A method according to claim 11, wherein the electroconductive metal element is placed underneath the cover element of the semiconductor component, inside said cover element.

13. (Previously Presented) A method according to claim 11, wherein the electroconductive metal element is attached to the cover element of the semiconductor component, outside said cover element.

14. (Previously Presented) A method according to claim 8, wherein the electroconductive metal element is induced in the cover element of the semiconductor component either chemically or electrochemically.

15. (Currently Amended) An arrangement including a mounting tray and at least one semiconductor component, wherein said at least one semiconductor component comprises a semiconductor element encased by a cover element having an integrated electroconductive metal element, where the electroconductive metal element is provided with at least one outlet that is constantly grounded to a ground plane of the mounting tray.

16. (Currently Amended) Apparatus for shielding a semiconductor element against electrostatic pulses, comprising:

means for covering the semiconductor element in a semiconductor component having an integrated electroconductive metal element; and

means for providing at least one outlet for the integrated electroconductive metal element, so that the at least one outlet is configured to constantly connect the electroconductive metal element to ground.

17. (Previously Presented) The apparatus of claim 16, wherein in the semiconductor component, there is integrated an electroconductive, planar metal element.

18. (Previously Presented) The apparatus of claim 16, wherein in the semiconductor component, there is integrated an electroconductive, loop-shaped metal element.

19. (Previously Presented) The apparatus of claim 16, wherein the electroconductive metal element is integrated as a permanent part of the semiconductor component.

20. (Previously Presented) The apparatus of claim 16, wherein the electroconductive metal element is integrated underneath the means for covering the semiconductor component, inside said cover element.